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List of Patents and Publications
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Information Disclosure Statement

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APPLICANT: Waldrip et al.

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REFERENCE DESIGNATION

Ex'r Init		U.S. Patent Documents			Sub Class	Class	File Date		
		Document No.	Date	Name			Translation	Yes	X No
		Foreign Patent Documents			Sub Class	Class	Translation		
		Document No.	Date	Name			Yes	X No	

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Examiner:

twan *Nguyen*

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